G494SD

SURFACE MOUNT, SCHOTTKY BARRIER DIODE

VOLTAGE 40V, CURRENT 0.4A

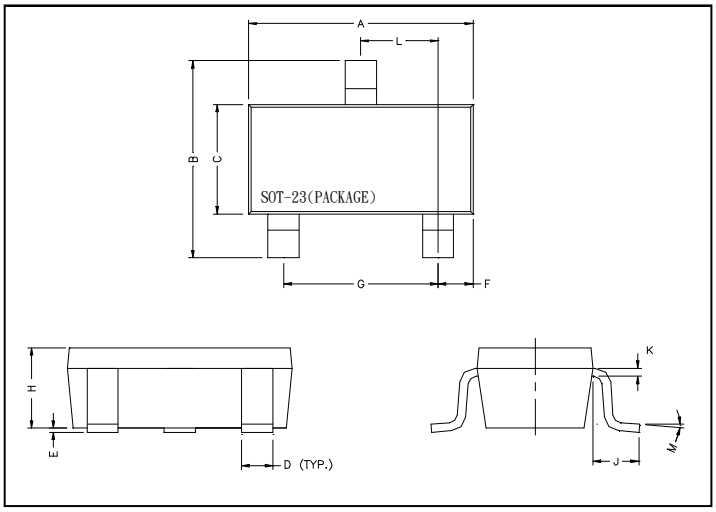
Description

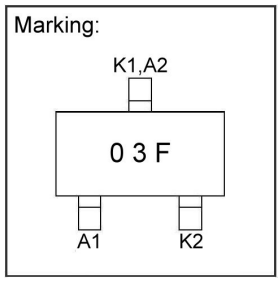
The G494SD is designed for low power rectification.

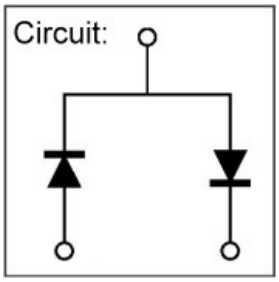
Feature

- Two diode with serial
- High reliability.

Package Dimensions







REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+125	℃
Storage Temperature	Tstg	-40 ~ +125	℃
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	40	V
Maximum RMS Voltage	V_{RMS}	28	V
Maximum DC Blocking Voltage	V_{DC}	25	V
Peak Forward Surge Current at 8.3mSec single half sine-wave	I_{FSM}	2.0	A
Typical Junction Capacitance between Terminal(Note1)	C_J	20	pF
Maximum Average Forward Rectified Current	Io	0.4	A
Total Power Dissipation	PD	225	mW

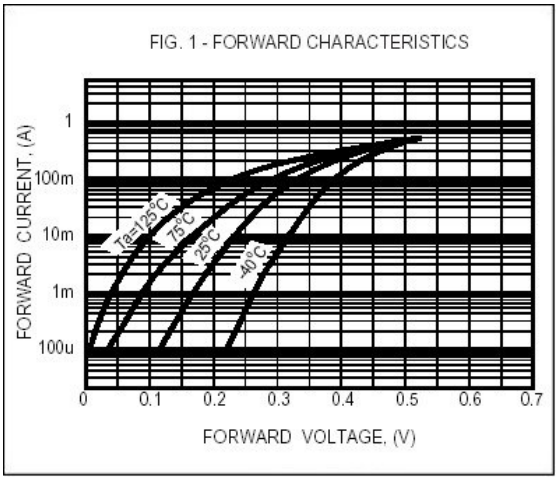
Electrical Characteristics (At Ta = 25℃ unless otherwise noted)

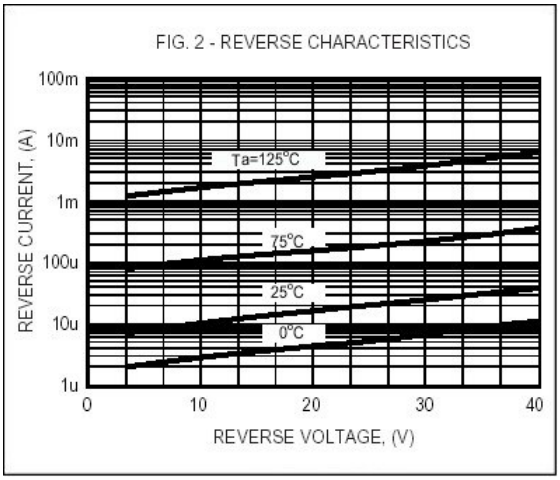
Characteristics	Symbol	Max.	Unit	Test Condition
Maximum Instantaneous Forward Voltage	$V_F(1)$	0.3	V	IF(1) = 10mA
Maximum Instantaneous Forward Voltage	$V_F(2)$	0.5	V	IF(2) = 200mA
Maximum Average Reverse Current	IR	70	uA	VR = 25V

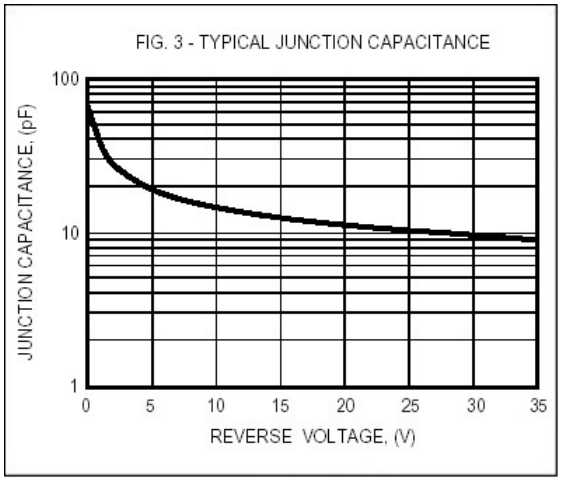
Notes: 1. Measured at 1.0MHz and applied reverse voltage of 10.0 volts.

2. ESD sensitive product handling required.

Characteristics Curve







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